

SELECTIVE ETCHING OF SILICON CARBIDE FILMS

ABSTRACT OF THE DISCLOSURE

A method of etching silicon carbide using a nonmetallic mask layer. The method includes providing a silicon carbide substrate; forming a non-metallic mask layer by applying a layer of material on the substrate; patterning the mask layer to expose underlying areas of the substrate; and etching the underlying areas of the substrate with a plasma at a first rate, while etching the mask layer at a rate lower than the first rate.

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